BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

As rescanning documents *will not* correct images, please do not report the images to the Image Problem Mailbox.

Amendments to the Abstract:

~~The present invention provides a display device which can reduce the~~ The irregularities of characteristics of a pair of transistors, which are prepared by a pseudo single crystallizing technique ~~and are used in a differential amplifying circuit or the like~~, are reduced. ~~The display device includes~~ To achieve this, semiconductor layers are formed on a substrate and ~~having~~ have pseudo single crystal regions therein, and a plurality of thin film ~~transistor~~ transistors are arranged ~~in the~~ inside ~~of~~ the pseudo single crystal regions. ~~Out of the plurality of thin film transistors, two~~ Two or more of the plurality of thin film transistors, which are required to exhibit small irregularities relative to each other as ~~the~~ characteristics ~~of the transistors~~ thereof, have the direction of ~~a~~ the length of the gates of the respective thin film transistors arranged ~~with~~ at an inclination of within ±20 degree with respect to the longitudinal direction of the strip-like grown crystals, and they are arranged such that, when channel regions of ~~the~~ respective thin film transistors are imaginarily extended in parallel to the growth direction of the strip-like grown crystals, at least portions of the channel regions are ~~superpose~~ superposed on each other.